ANYO SEMICONDUCTOR	CORP		TSE D	7997076 00 <u>0</u> 5	151 5
2SD1656		21		T-33-11	
	20	39	NPN Triple Di Silic	ffused Planar on Transistor	
	Col	or TV Horiz			ę
(£)17548		Out	tput Appl	cations	
Applications . High-voltage, power sw	itching				
Features . Fast speed (t _f max=0.4u . High reliability (Adop . High breakdown voltage . Micaless package facil	tion of H (V _{CBO} =15	00V).	•		
Absolute Maximum Ratings a Collector to Base Voltag				unit 1500 V	
Collector to Emitter Vol Emitter to Base Voltage	tage V _{CE}	0		800 V 6 V	
Collector Current		-		6 A	
Peak Collector Current Collector Dissipation	icp PC Tj	T _C =25 [°] C		16 A	
Junction Temperature	r Ti	1C=25 C		60 W 150 ^O C	
Storage Temperature	Tst,		-55 to		
Electrical Characteristics	at Ta=25	°C	min t	yp max unit	
Collector Cutoff Current		V _{CB} =800V,I _E =0	*	10 uA	•
Emitter Cutoff Current	I _{EBO}	$V_{\rm HD}=5V \cdot I_{\rm C}=0$		1 mA	
DC Current Gain	n _{FE}	$V_{CE} = 5V, I_C = 1A$	8		
Gain Bandwidth Product	f _m	V _{CE} =5V, I _C =1A V _{CE} =10V, I _C =1A		3 MHz	
Collector to Emitter	V _{CE(sat)}	$I_{C}=5A, I_{B}=1A$.5 V	
Saturation Voltage					
Base to Emitter	VBE(sat)	I _C =5A,I _B =1A		1.5 V	
Saturation Voltage Collector to Base	ν	T 5m1 T -0	1500	v	
Breakdown Voltage	*(BR)CBO	$I_{C}=5mA, I_{E}=0$	- 1500	V	
Collector to Emitter Breakdown Voltage	V _(BR) ceo	I_{C} =100mA, R_{BE} =00	800	V	
Emitter to Base Breakdown Voltage	V(BR)EBO	I _E =200mA,I _C =0	7	v	
Fall Time	^t f	I _C =5A,I _{B1} =1A, I _{B2} =-2A		0.4 us	
Switching Time Test Circui		ase Outline 2039			
PW≖20us,Duty≦1% OUTPUT	(1	L. 8.0	22.0 20.6	3.5	
-1B2	•	5.0			
181>					
		9ª -∲	L <u>2.6</u> B	∍ † ₈	
AL AO			1 2.0	∍ı∾ []]	
50,≢ ,¥VR		-	21.0 21.0	E: Emitter	
				C: Collector	
		با 1 %	/	B: Base	
VBE=-5V VCC=200V		a a a a a a a a a a a a a a a a a a a		SANYO: TO 3PML	
		•1			
			•		

5277KI/D244KI,TS No. 1754-1/3 1491

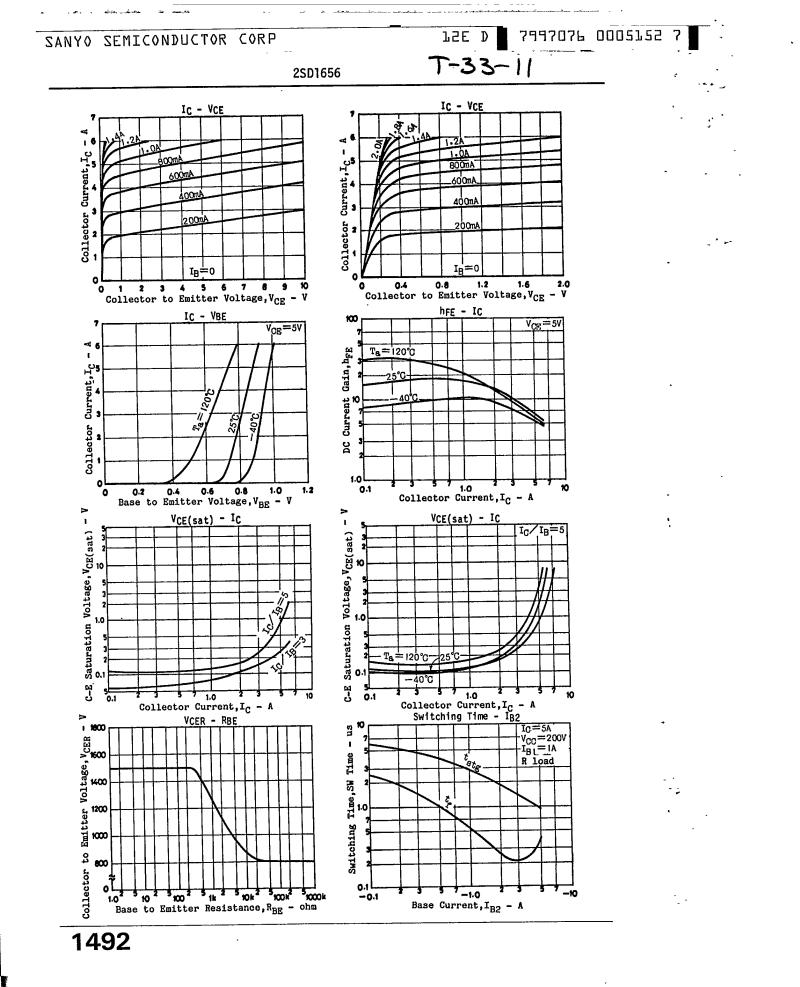
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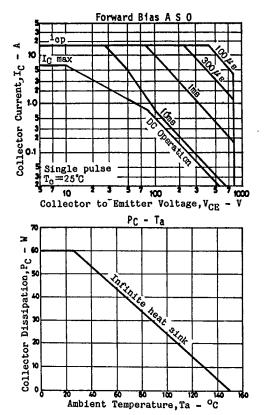
SANYO SEMICONDUCTOR CORP

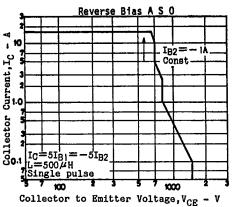
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2SD1656

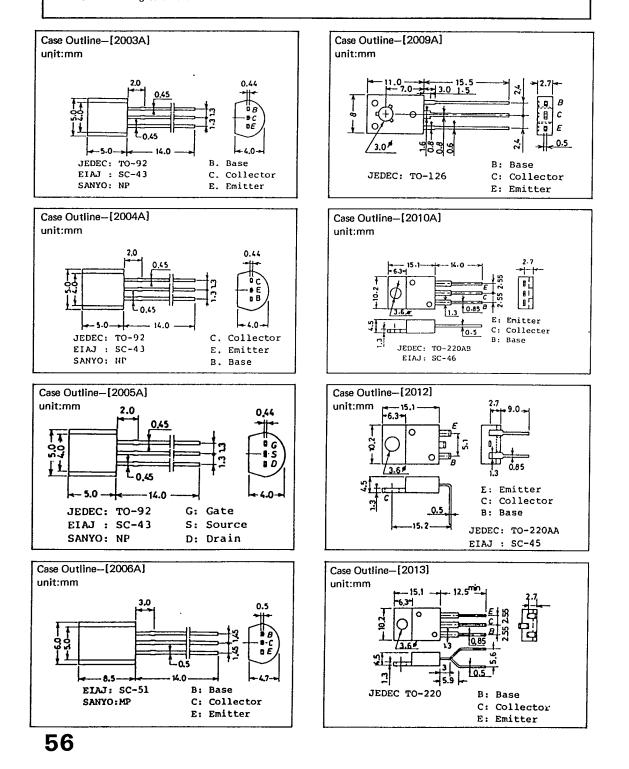
SANYO SEMICONDUCTOR CORP

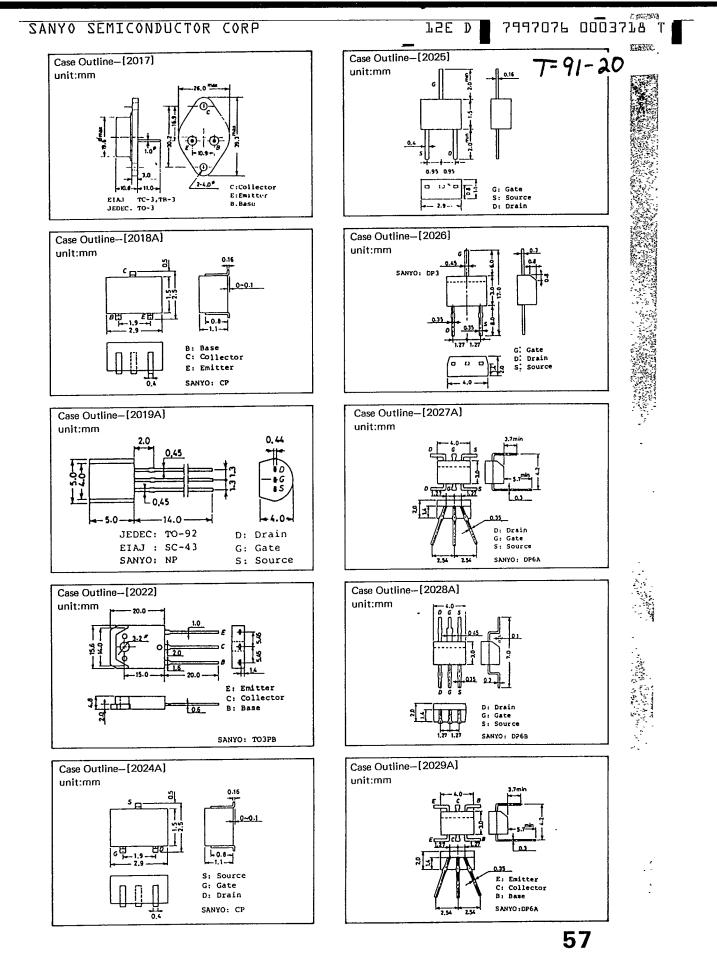
15E D 7997076 0003717 A

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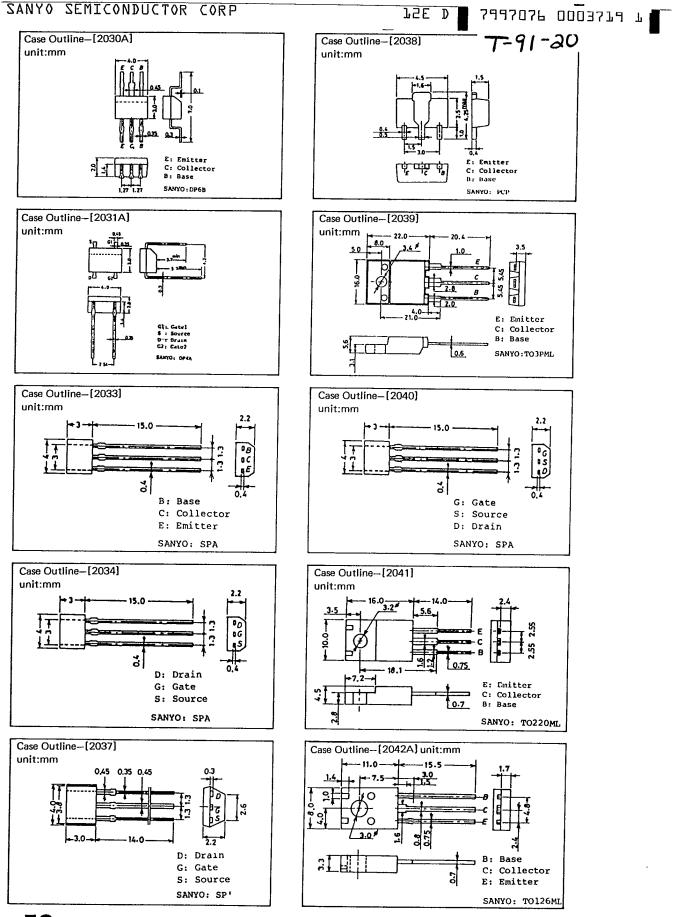
CASE OUTLINES AND ATTACHMENTS

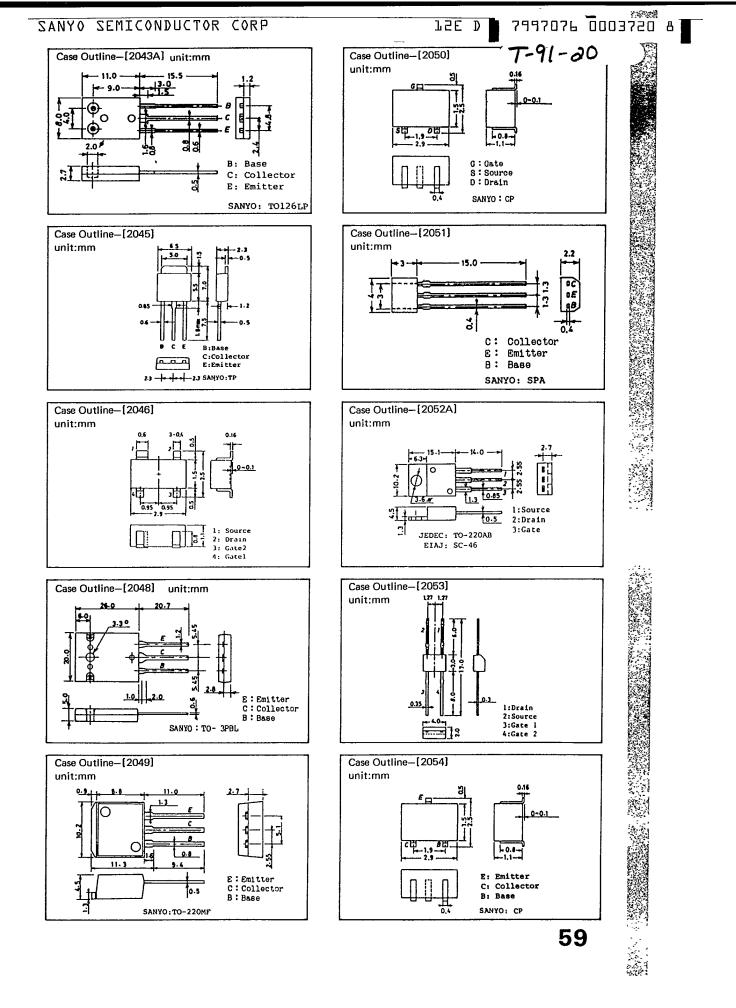
- •All of Sanyo Transistor case outlines are illustrated below.
- •All dimensions are in mm, and dimensions which are not followed by min. or max. are represented by typical values.
- •No marking is indicated.

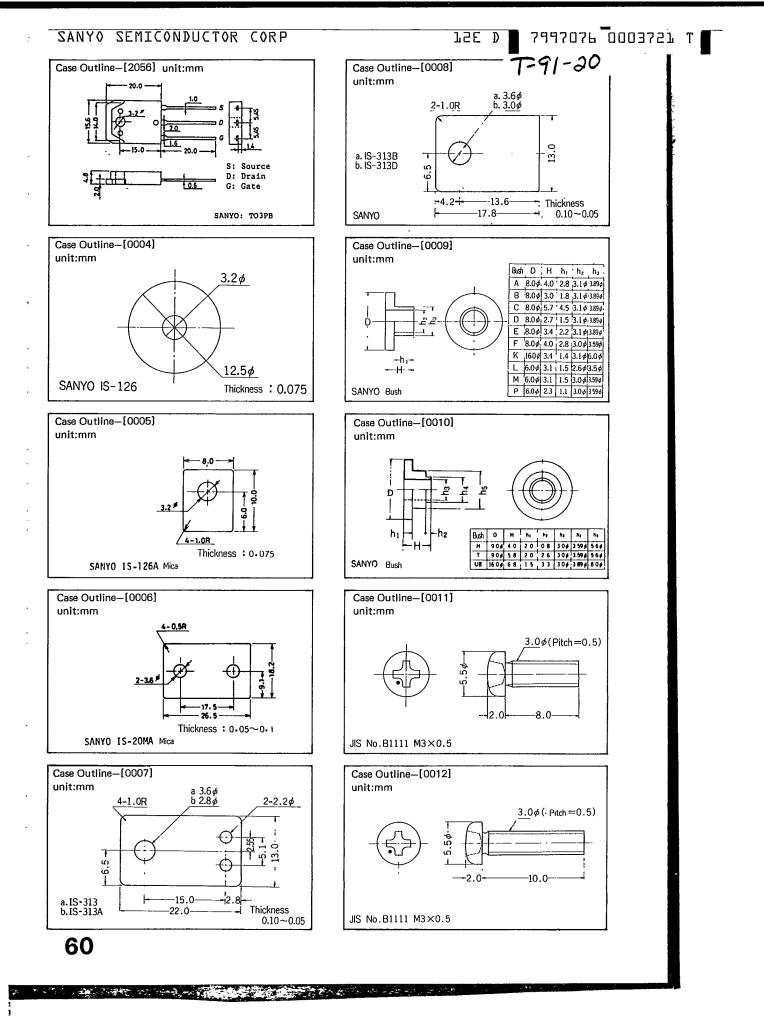


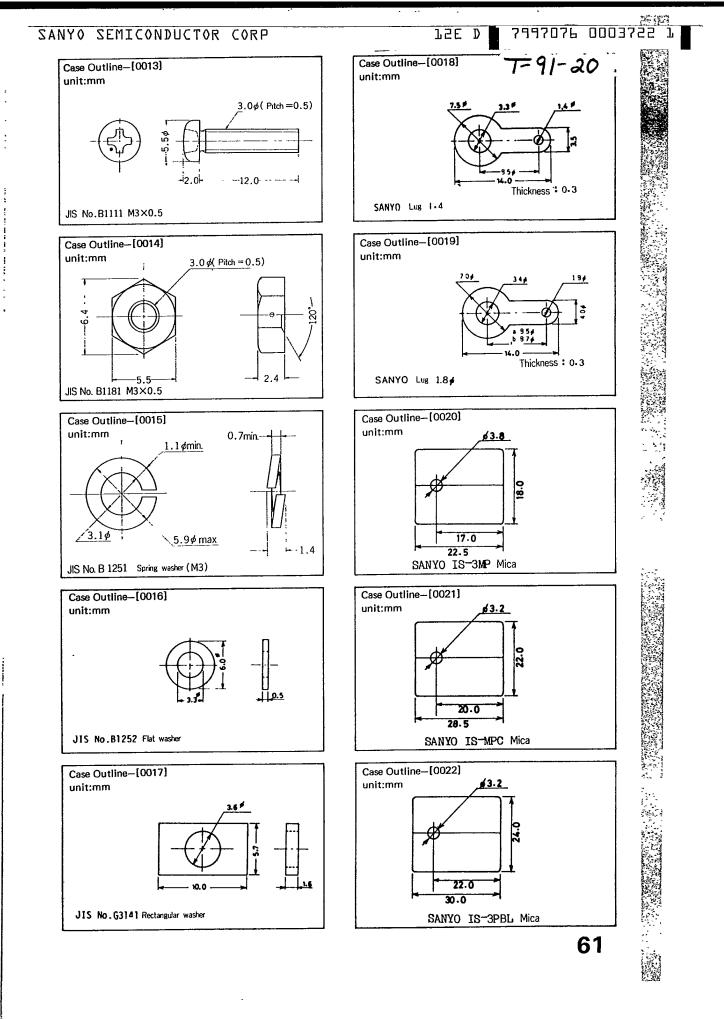


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